

Boosting Voltage Regulators

■ GENERAL DESCRIPTION

The XC62E series are a group of positive output voltage regulators that can supply up to 1A of output current using an external transistor. Low power and high accuracy are achieved through CMOS process and laser trimming technologies. The series consists of a high precision voltage reference, an error correction circuit and a short-circuit protected output driver. In stand-by mode, supply current can be dramatically cut. Since the input-output voltage differential is small, loss control efficiency is good.

The XC62E is particularly suited for use with battery operated portable products, and products where supply current regulation is required.

The series are available in an ultra small SOT-25 package.

In connection with the CE function, apart from the negative logic XC62EP series, a positive logic XC62ER series (custom) is also available.

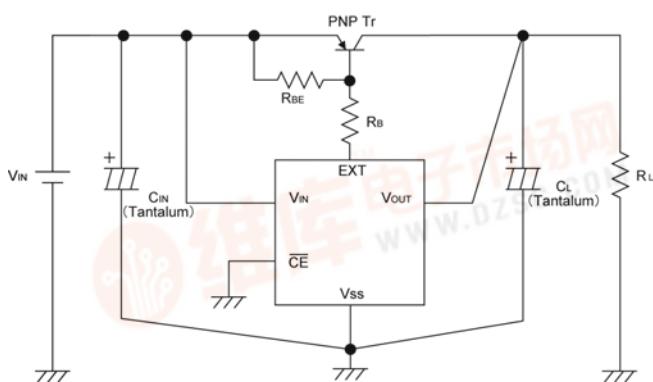
■ APPLICATIONS

- Portable cameras and video recorders
- Battery powered equipment
- Palmtops
- Reference voltage sources

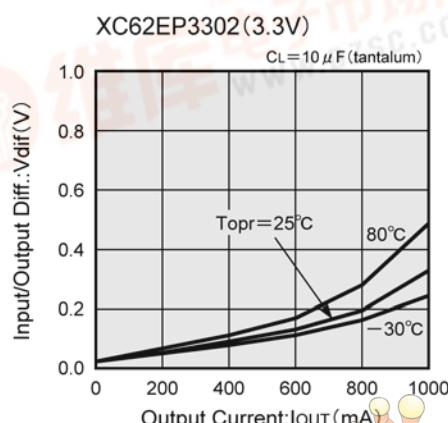
■ FEATURES

Dropout Voltage	: 0.1A@100mA (Performance depends on the external transistor characteristics.)
Maximum Output Current	: 1000mA
Output Voltage Range	: 1.5V~6.0V in 100mV increments
Highly Accurate	: Setting voltage $\pm 2\%$
Low Power Consumption	: 50 μ A (V _{OUT} =5.0V) (TYP.) : 0.2 μ A (Stand-by) (TYP.)
Output Voltage Temperature Characteristics	
: ± 100 ppm/ $^{\circ}$ C (TYP.)	
Line Regulation	: 0.1%/V (TYP.)
CMOS Low Power Consumption	
Package	: SOT-25
Environmentally Friendly	: EU RoHS Compliant

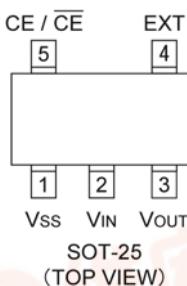
■ TYPICAL APPLICATION CIRCUIT



■ TYPICAL PERFORMANCE CHARACTERISTICS



■PIN CONFIGURATION



■PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	Vss	Ground
2	VIN	Supply Voltage Input
3	Vout	Regulated Voltage Output
4	EXT	Base Current Control
5	CE/CE	Chip Enable

■FUNCTION

SERIES	CE	OUTPUT VOLTAGE
XC62ER	H	ON
	L	OFF
XC62EP	H	OFF
	L	ON

H=High level

L=Low level

■PRODUCT CLASSIFICATION

● Ordering Information

XC62E①②③④⑤⑥⑦-⑧^(*)

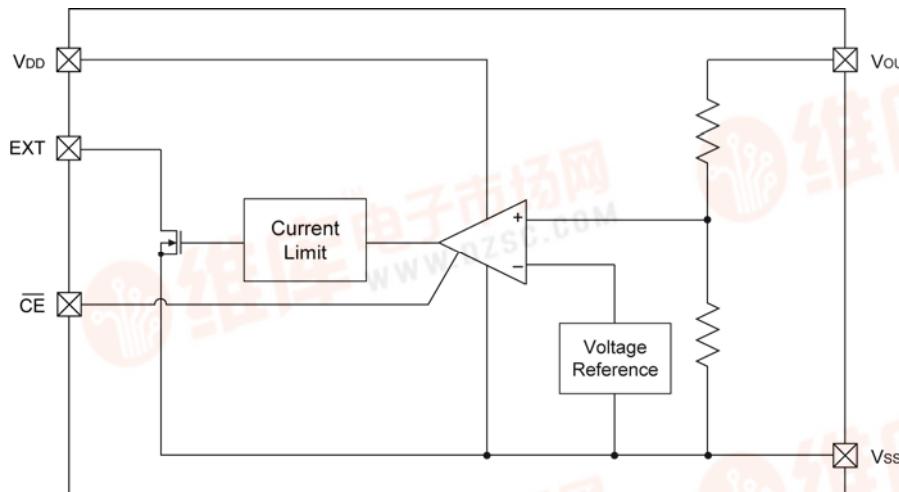
DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION
①	CE Pin Logic	R	Positive
		P	Negative
②③	Output Voltage	15 ~ 60	e.g. VOUT 1.5V→②=1, ③=5 VOUT 6.0V→②=6, ③=0
④	Temperature Characteristics	0	±100ppm (TYP.)
⑤	Output Voltage Accuracy	2	±2%
⑥⑦-⑧	Packages Taping Type ^(*)	MR	SOT-25
		MR-G	SOT-25

^(*) The “-G” suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

^(*) The device orientation is fixed in its embossed tape pocket. For reverse orientation, please contact your local Torex sales office or representative. (Standard orientation: ⑥R-⑧, Reverse orientation: ⑥L-⑧)

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■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

T_a = 25°C

PARAMETER	SYMBOL	RATINGS	UNITS
V _{IN} Input Voltage	V _{IN}	12.0	V
V _{OUT} -Output Voltage	V _{OUT}	V _{SS} -0.3~V _{IN} +0.3	V
CE/CE Input Voltage	V _{CE}	V _{SS} -0.3~V _{IN} +0.3	V
EXT Output Voltage	V _{EXT}	12.0	V
EXT Output Current	I _{EXT}	50	mA
Power Dissipation	P _d	150	mW
Operating Temperature Range	T _{opr}	-30~+80	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

■ ELECTRICAL CHARACTERISTICS

XC62EP3002 VOUT(T)=3.0V (*1)

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Voltage	VOUT(E) (*2)	IOUT=50mA VIN=4.0V	2.940	3.000	3.060	V
Maximum Output Current*	IOUT max	VIN=4.0V	-	1000	-	mA
Load Regulation (*6)	ΔVOUT	VIN=4.0V 1mA≤IOUT≤100mA	-60	-	60	mV
Dropout Voltage (*3)	Vdif	IOUT=100mA	-	100	-	mV
Supply Current 1	I _{SS1}	VIN=4.0V, VCE=VSS	-	50	80	μA
Supply Current 2	I _{SS2}	VIN=8.0V, VCE=VIN	-	-	0.6	μA
Line Regulation (*6)	$\frac{\Delta VOUT}{\Delta VIN \cdot VOUT}$	IOUT=50mA 4.0V≤VIN≤8.0V	-	0.1	0.3	%V
Input Voltage	ΔVIN		-	-	8.0	V
Output Voltage Temperature Characteristics (*6)	$\frac{\Delta VOUT}{\Delta Topr \cdot VOUT}$	IOUT=10mA -30°C≤Topr≤80°C	-	±100	-	ppm/°C
EXT Output Voltage	V _{EXT}		-	-	8.0	V
EXT Leak Current	I _{LEAK}		-	-	0.5	μA
CE "High" Level Voltage	V _{CEH}		1.5	-	-	V
CE "Low" Level Voltage	V _{CEL}		-	-	0.25	V
CE "High" Level Current	I _{CEH}	V _C =VIN	-	-	0.1	μA
CE "Low" Level Current	I _{CEL}	V _C =VSS	-0.2	-0.05	0	μA

The characteristics for the XC62ER series are the same as above except for the CE operating logic, which is the opposite.

NOTE:

*1: VOUT(T)=Specified output voltage.

*2: VOUT(E)=Effective output voltage (i.e. the output voltage when "VOUT(T)+1.0V" is provided at the VIN pin while maintaining a certain IOUT value).

*3: Vdif= {VIN1 (*5)-VOUT1 (*4)}

*4: VOUT1=A voltage equal to 98% of the output voltage whenever an amply stabilized IOUT {VOUT(T)+1.0V} is input.

*5: VIN1=The input voltage when VOUT1 appears as input voltage is gradually decreased.

*6: The characteristics for the parameters are liable to vary depending on which transistor is used.

Please use a transistor with a low saturation voltage level and hFE equal to 100 or more.

*7: The maximum output current value is not a value representing continuous output due to the limitations of the 2AS1213 transistor's power dissipation.

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■ ELECTRICAL CHARACTERISTICS (Continued)

XC62EP4002 VOUT(T)=4.0V(*1)

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Voltage	VOUT(E) (*2)	IOUT=50mA VIN=5.0V	3.920	4.000	4.080	V
Maximum Output Current (*6)	IOUT max	VIN=5.0V	-	1000	-	mA
Load Regulation (*6)	ΔVOUT	VIN=5.0V 1mA≤IOUT≤100mA	-60	-	60	mV
Dropout Voltage (*3)	Vdif	IOUT=100mA	-	100	-	mV
Supply Current 1	I _{SS1}	VIN=5.0V, V _{CE} =V _{SS}	-	50	80	μA
Supply Current 2	I _{SS2}	VIN=8.0V, V _{CE} =VIN	-	-	0.6	μA
Line Regulation (*6)	ΔVOUT ΔVIN · VOUT	IOUT=50mA 5.0V≤VIN≤8.0V	-	0.1	0.3	%V
Input Voltage	VIN		-	-	8.0	V
Output Voltage Temperature Characteristics (*6)	ΔVOUT ΔTopr · VOUT	IOUT=10mA -30°C≤Topr≤80°C	-	±100	-	ppm/°C
EXT Output Voltage	V _{EXT}		-	-	8.0	V
EXT Leak Current	I _{LEAK}		-	-	0.5	μA
CE "High" Level Voltage	V _{C EH}		1.5	-	-	V
CE "Low" Level Voltage	V _{C EL}		-	-	0.25	V
CE "High" Level Current	I _{C EH}	V _{CE} =VIN	-	-	0.1	μA
CE "Low" Level Current	I _{C EL}	V _{CE} =V _{SS}	-0.2	-0.05	0	μA

XC62EP4002 VOUT(T)=5.0V(*1)

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Voltage	VOUT(E) (*2)	IOUT=50mA VIN=6.0V	4.940	5.000	5.100	V
Maximum Output Current (*6)	IOUT max	VIN=6.0V	-	1000	-	mA
Load Regulation (*6)	ΔVOUT	VIN=6.0V 1mA≤IOUT≤100mA	-60	-	60	mV
Dropout Voltage (*3)	Vdif	IOUT=100mA	-	100	-	mV
Supply Current 1	I _{SS1}	VIN=6.0V, V _{CE} =V _{SS}	-	50	80	μA
Supply Current 2	I _{SS2}	VIN=8.0V, V _{CE} =VIN	-	-	0.6	μA
Line Regulation (*6)	ΔVOUT ΔVIN · VOUT	IOUT=50mA 6.0V≤VIN≤8.0V	-	0.1	0.3	%V
Input Voltage	VIN		-	-	8.0	V
Output Voltage Temperature Characteristics (*6)	ΔVOUT ΔTopr · VOUT	IOUT=10mA -30°C≤Topr≤80°C	-	±100	-	ppm/°C
EXT Output Voltage	V _{EXT}		-	-	8.0	V
EXT Leak Current	I _{LEAK}		-	-	0.5	μA
CE "High" Level Voltage	V _{C EH}		1.5	-	-	V
CE "Low" Level Voltage	V _{C EL}		-	-	0.25	V
CE "High" Level Current	I _{C EH}	V _{CE} =VIN	-	-	0.1	μA
CE "Low" Level Current	I _{C EL}	V _{CE} =V _{SS}	-0.2	-0.05	0	μA

The characteristics for the XC62ER series are the same as above except for the CE operating logic, which is the opposite.

Note: *1. VOUT(T)=Specified output voltage.

*2. VOUT(E)=Effective output voltage (i.e. the output voltage when "VOUT(T)+1.0V" is provided at the VIN pin while maintaining a certain IOUT value).

*3. Vdif= {VIN1 (*5)-VOUT1 (*4)}

*4. VOUT1= A voltage equal to 98% of the output voltage whenever an amply stabilized IOUT {VOUT(T)+1.0V} is input.

*5. VIN1= The input voltage when VOUT1 appears as input voltage is gradually decreased.

*6. The characteristics for the parameters are liable to vary depending on which transistor is used.

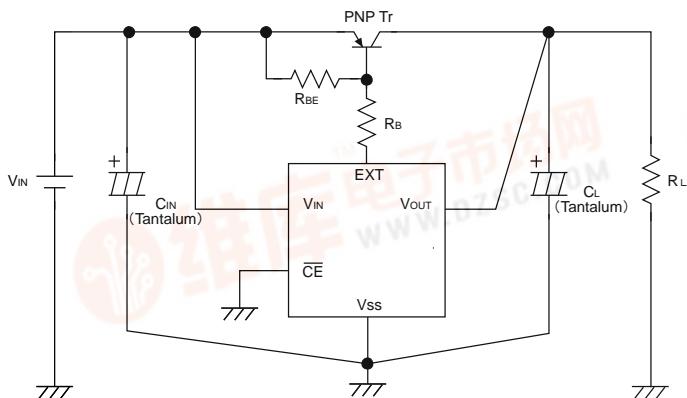
Please use a transistor with a low saturation voltage level and hFE equal to 100 or more.

*7. The maximum output current value is not a value representing continuous output due to the limitations of the 2AS1213 transistor's power dissipation.



■ TYPICAL APPLICATION CIRCUIT

● Standard Circuit



External Components:

PNP Tr.: 2SA1213

RBE: 20kΩ ~ 47kΩ

RB: Please refer to Note 2 on the following page.

CIN: 10μF (Tantalum)

CL: 47μF (Tantalum) 10μF minimum

■ OPERATIONAL EXPLANATION

Output voltage (VOUT) can be fixed by revising the external transistor's base current. This can be done by comparing the detected voltage level and the setting voltage power supply level.

With the XC62EP (CE negative voltage), if a voltage above the \overline{CE} pin's "H" level is applied, the IC will enter stand-by mode where the base and differential amplifier's currents are regulated.

■ NOTES ON USE

1. PNP Transistor

The selection of a transistor should take into account output current, input voltage and power dissipation for each specific application. It is recommended that a transistor that has a low output saturated voltage (VCE) and high hFE characteristics be used.

2. RB Resistor

Although the IC unit is protected by a base current remitter circuit, it is recommended that a resistor (RB) be connected between the transistor's base and the IC's EXT pin to protect the transistor.

Required output current can be calculated using the following equation although characteristic variations and conditions of use should be carefully checked before use. The following equation also indicates the conditions needed to obtain I_{OUT} (MAX.) at V_{IN} (MIN.). However, the larger the input current, the larger the output current (I_{OUT}) that can be obtained.

$$\frac{V_{IN}(\text{MIN.})-1.2(V)}{R_B} - \frac{0.7(V)}{R_{BE}} > \frac{I_{OUT}(\text{MAX.})}{hFE}$$

3. RBE Resistor, CL Capacitor

To prevent oscillation due to output load variation, use of a phase compensation capacitor CL is recommended. Please use a Tantalum capacitor of at least 10mF. Please also use an RBE resistor of less than 47kΩ.

An RBE resistor of between 20kΩ and 47kΩ is recommended for less power consumption.

4. Input Impedance

In order to control oscillation brought about as a result of impedance at the power supply line, connect a capacitor of 10μF or more (Tantalum) between the external transistor's emitter and the ground pin.

● Protection Circuit

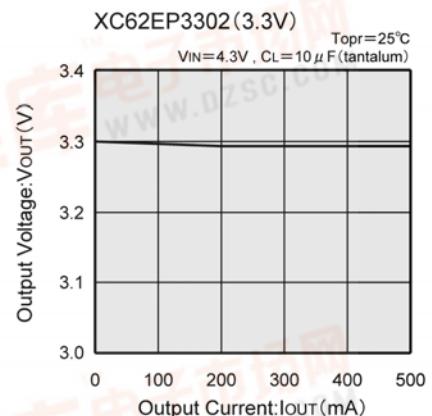
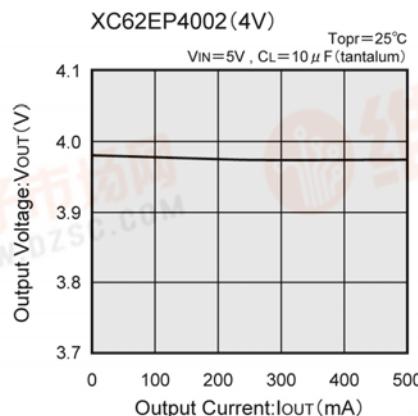
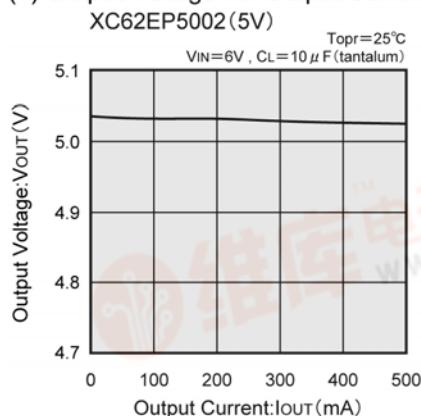
The built-in protection circuit is to protect the IC only. Therefore to prevent output shorts and overshoot current through the transistor, use of a resistor RB or an overshoot current protection circuit is recommended.

Care should also be taken with the transistor's power dissipation.

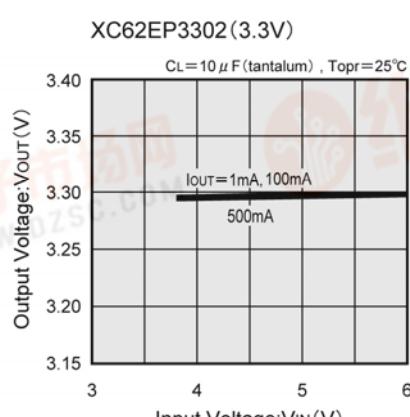
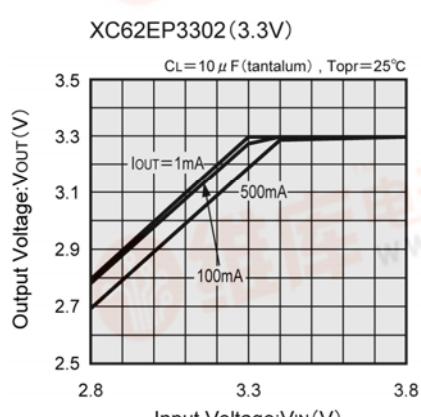
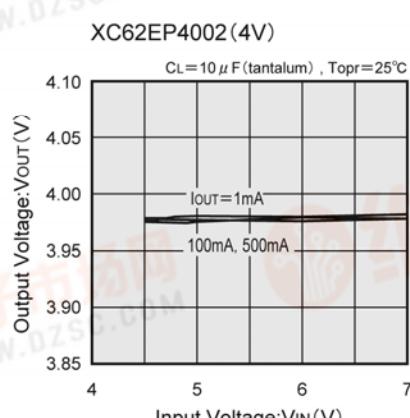
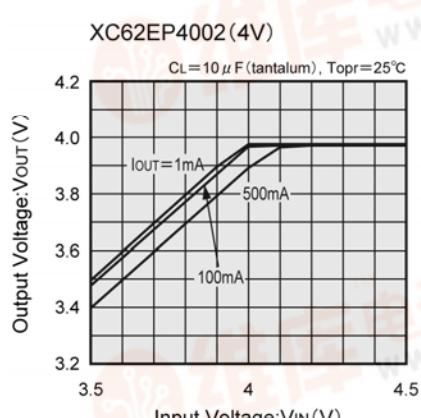
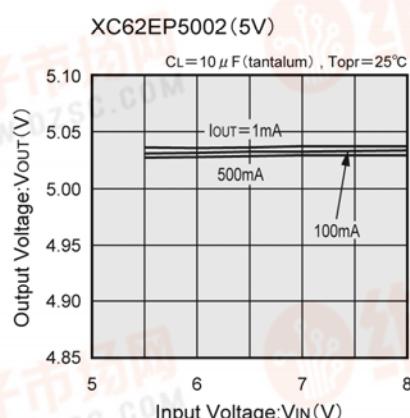
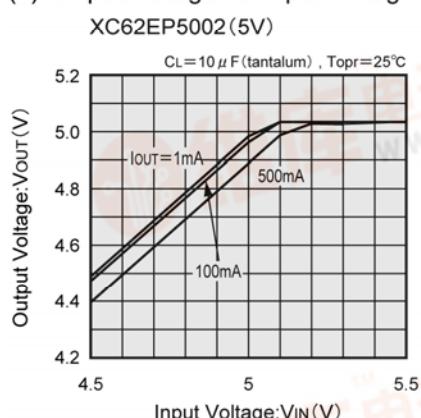
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■ TYPICAL PERFORMANCE CHARACTERISTICS

(1) Output Voltage vs. Output Current



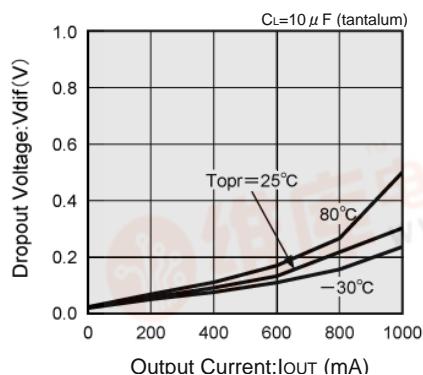
(2) Output Voltage vs. Input Voltage



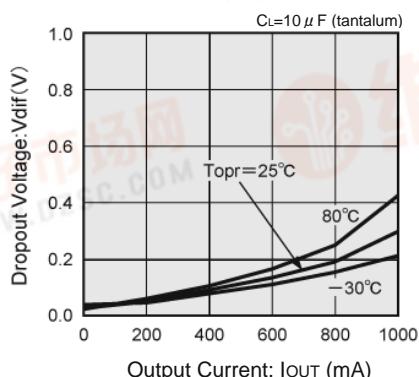
■ TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(3) Dropout Voltage vs. Output Current

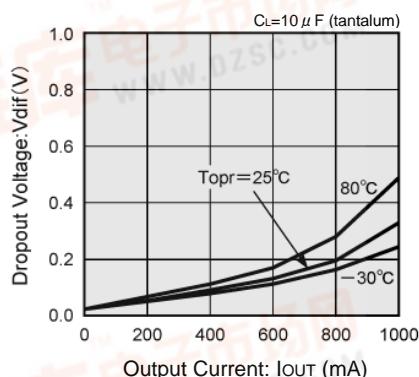
XC62EP5002 (5V)



XC62EP4002 (4V)

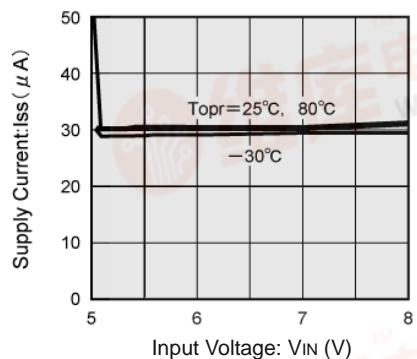


XC62EP3302 (3.3V)

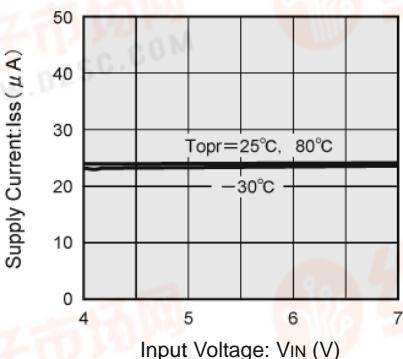


(4) Supply Current vs. Input Voltage

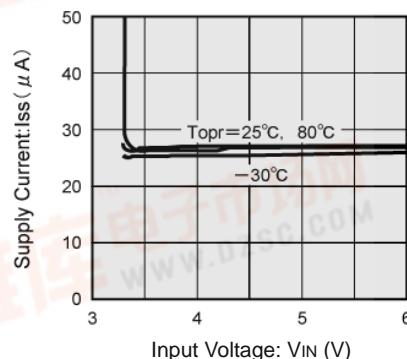
XC62EP5002 (5V)



XC62EP4002 (4V)

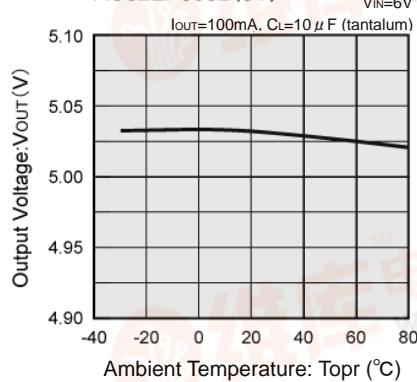


XC62EP3302 (3.3V)

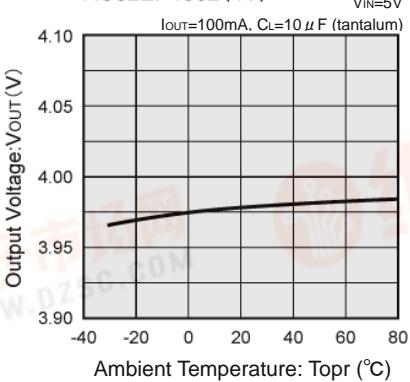


(5) Output Voltage vs. Ambient Temperature

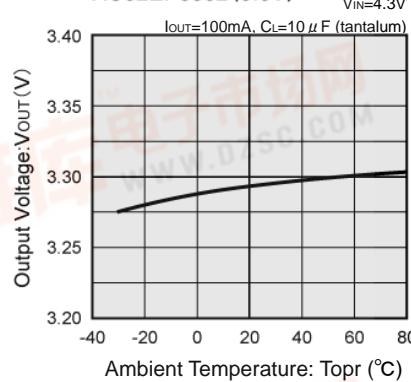
XC62EP5002 (5V)



XC62EP4002 (4V)

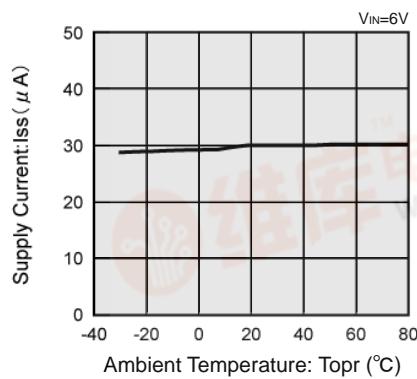


XC62EP3302 (3.3V)

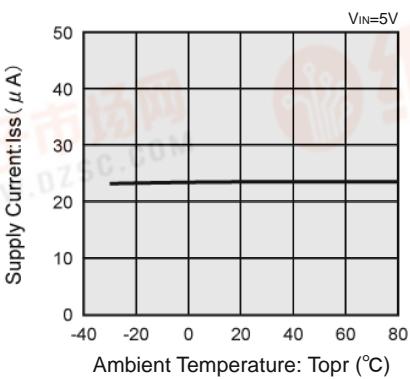


(6) Supply Current vs. Ambient Temperature

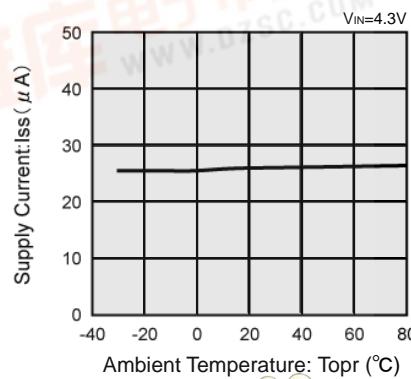
XC62EP5002 (5V)



XC62EP4002 (4V)



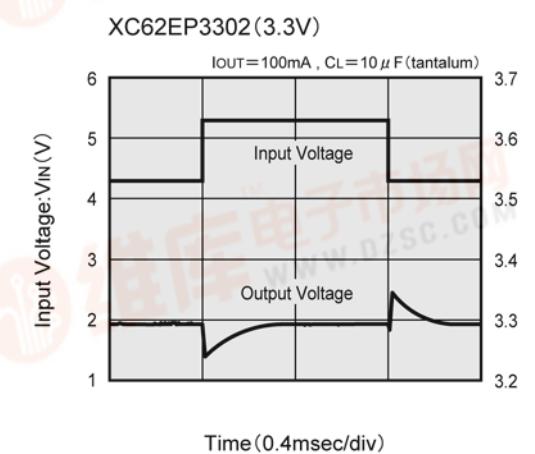
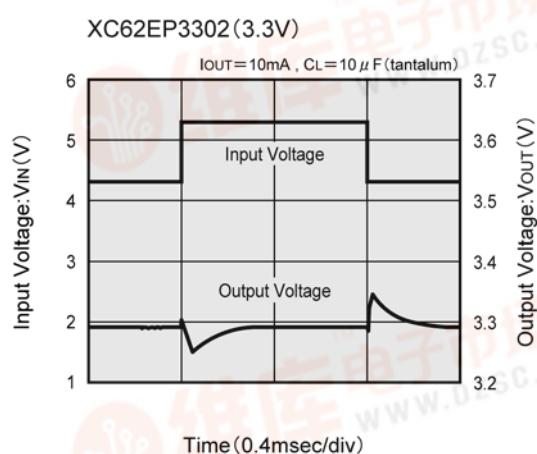
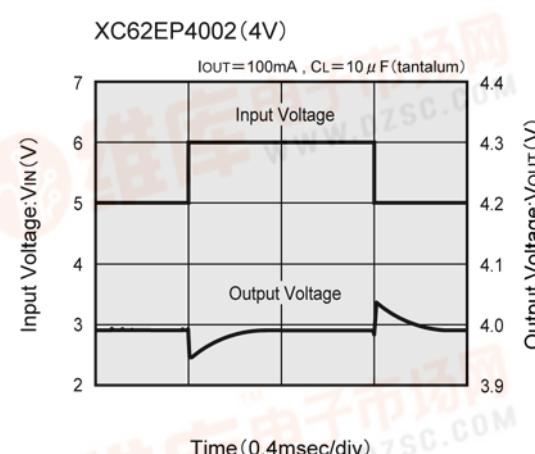
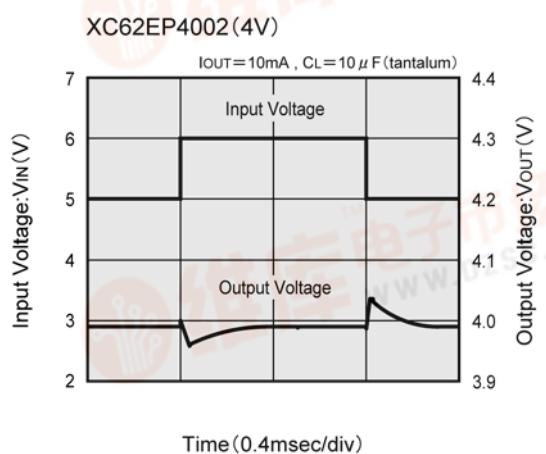
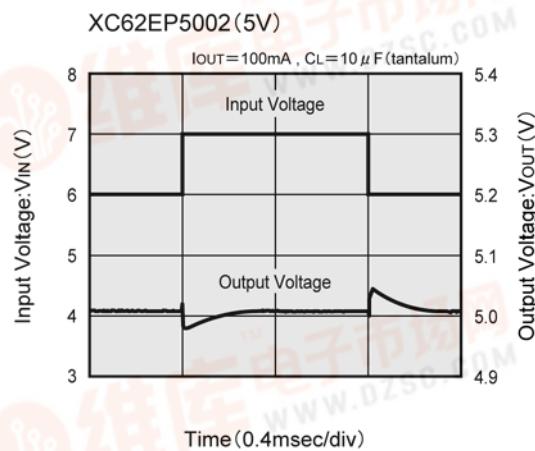
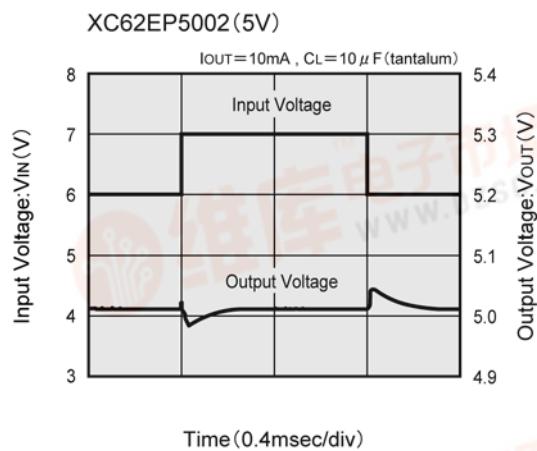
XC62EP3302 (3.3V)



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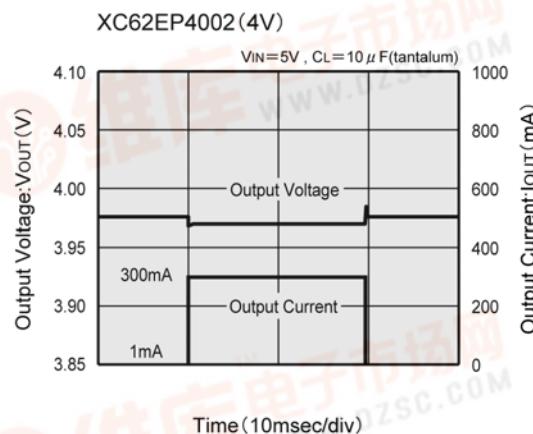
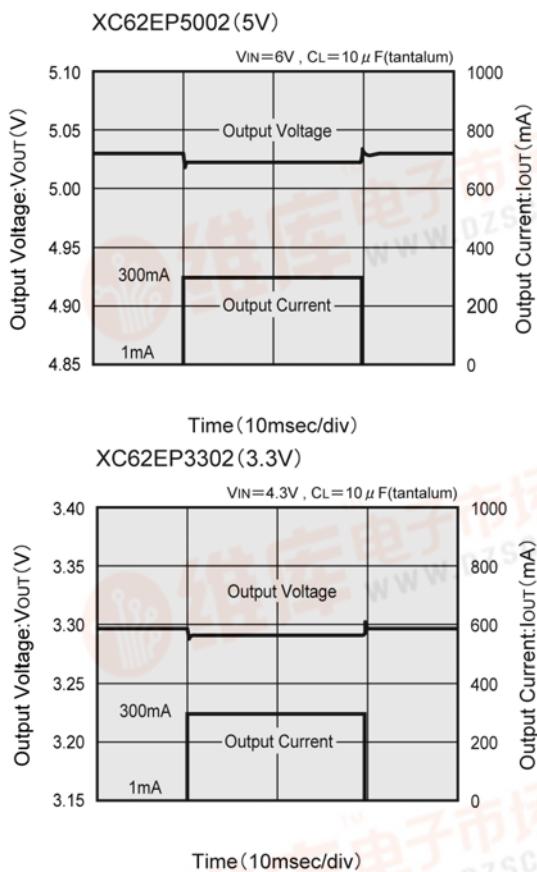
■ TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(7) Input Transient Response

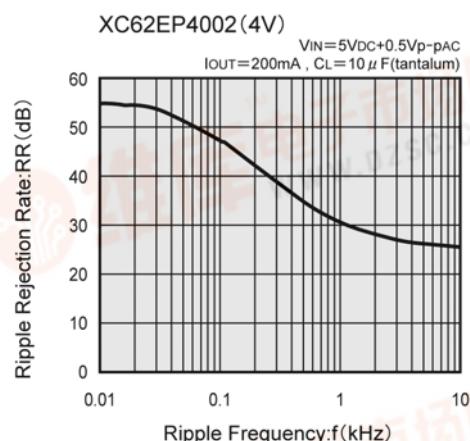
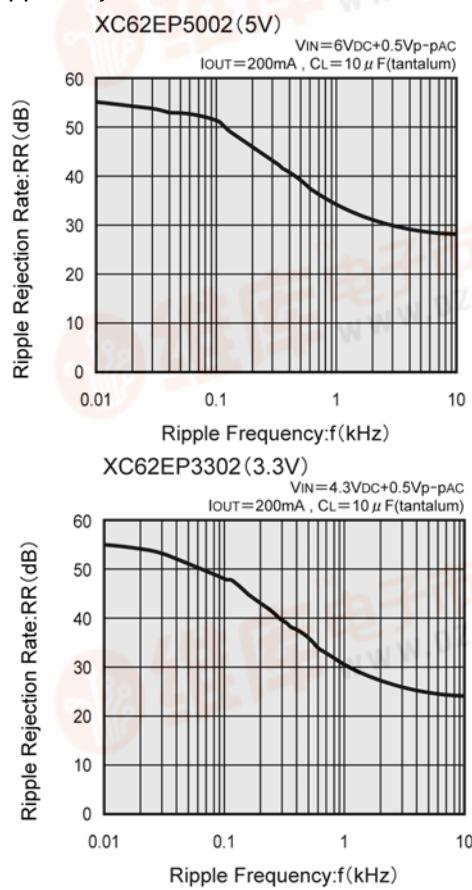


■ TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(8) Load Transient Response



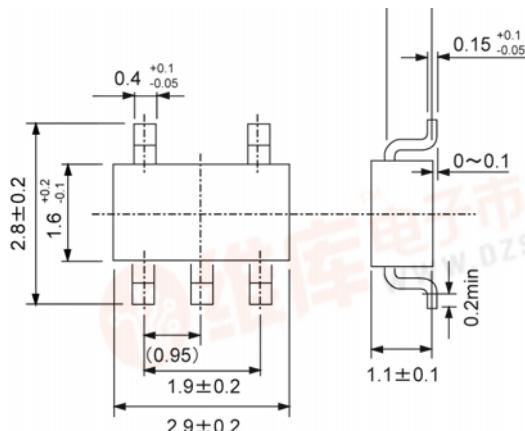
(9) Ripple Rejection Rate



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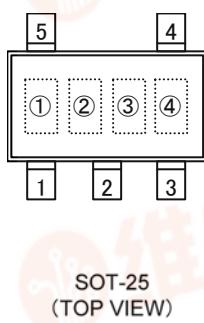
■PACKAGING INFORMATION

●SOT-25



■MARKING RULE

●SOT-25



① not used

② represents integer of output voltage

MARK (XC62ER Type)	VOLTAGE (V)	MARK (XC62EP Type)	VOLTAGE (V)
2	2.x	2	2.x
3	3.x	3	3.x
4	4.x	4	4.x
5	5.x	5	5.x
6	6.x	6	6.x

③ represents decimal number of output voltage

MARK (XC62ER Type)	VOLTAGE (V)	MARK (XC62EP Type)	VOLTAGE (V)
0	x.0	0	x.0
1	x.1	1	x.1
2	x.2	2	x.2
3	x.3	3	x.3
4	x.4	4	x.4
5	x.5	5	x.5
6	x.6	6	x.6
7	x.7	7	x.7
8	x.8	8	x.8
9	x.9	9	x.9

④ based on internal standards

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